
Term project (Ver 1.1)

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Revision history

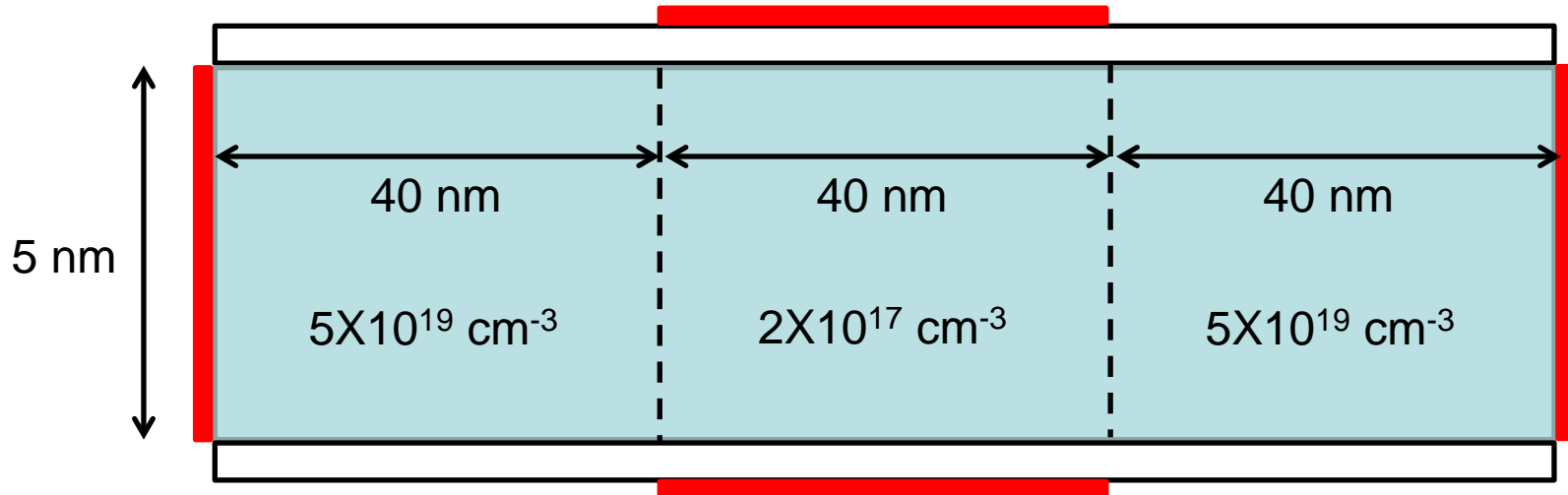
- Nov 25: Ver 1.0
 - Initial version
- Nov 26: Ver 1.1
 - Modify the Boltzmann equation part. Elastic scattering.

Term project (1)

- Due: AM08:00, December 17 (No delayed submission)
- Your code and report should be submitted.
- There are many steps in the term project.
 - Nonlinear Poisson
 - Drift-diffusion
 - Schrödinger
 - Boltzmann

Term project (2)

- Double-gate
 - 5-nm-thick silicon & 0.5-nm-thick oxide at both sides
 - 40-nm-long gate (Workfunction: 4.3 eV)



Term project (3)

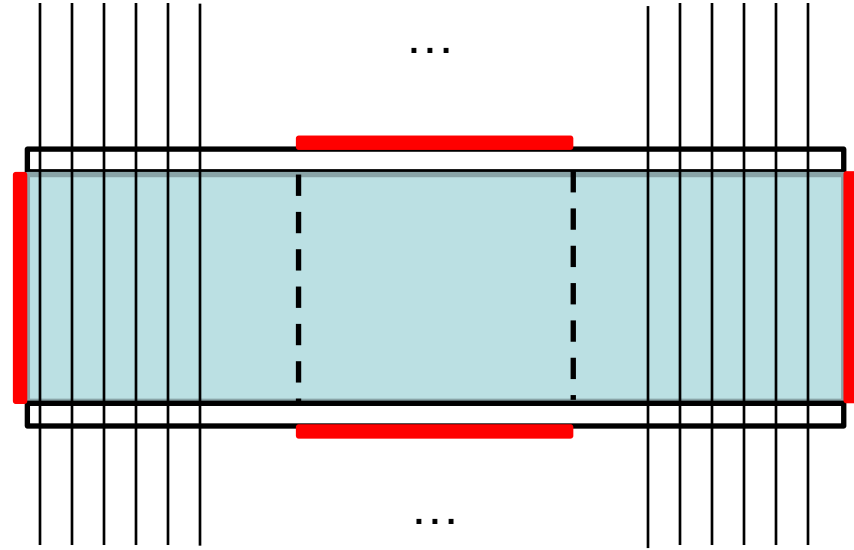
- Step1
 - Solve the nonlinear Poisson equation for the double-gate structure.
 - $V_S = V_D = 0$ and V_G varies from 0 V to 1 V. (0.1 V step)
 - Draw ϕ and n . (3D plot)

Term project (4)

- Step2
 - Solve the drift-diffusion equation for the double-gate structure.
 - Self-consistent simulation is mandatory.
 - $V_S = 0$
 - V_G varies from 0 V to 1 V. (0.1 V step)
 - V_D varies from 0 V to 1 V. (0.1 V step)
 - For each V_G , draw the drain current (I_D) as a function of V_D .
 - The electron mobility is assumed to be 1430 cm²/V sec.

Term project (5)

- Step3
 - Solve the Schrödinger equation.
 - Use ϕ obtained in Step2.
 - (Non-self-consistent simulation)
 - $V_S = 0$
 - Consider V_G of 0.1 V and 0.5 V.
 - Consider V_D of 0.1 V and 0.5 V.
 - Consider three different valleys.
 - Calculate the lowest subband for each slab. ←



Term project (6)

- Step4
 - Solve the Boltzmann equation. (Only an elastic scattering with $\tau = 0.1$ psec is considered.)
 - For each valley, only the lowest subband is considered.
 - Use ϕ obtained in Step2. (Non-self-consistent simulation)
 - $V_S = 0$
 - Consider V_G of 0.1 V and 0.5 V.
 - Consider V_D of 0.1 V and 0.5 V.
 - Calculate the drain current (I_D) for the four cases.
 - For each case, draw f_0 of each valley. (3D plot)